

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Avalanche characteristic.
2. Medium current, low forward voltage.
3. High frequency, Fast recovery.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. X-ray power supply.

MECHANICAL DATA:

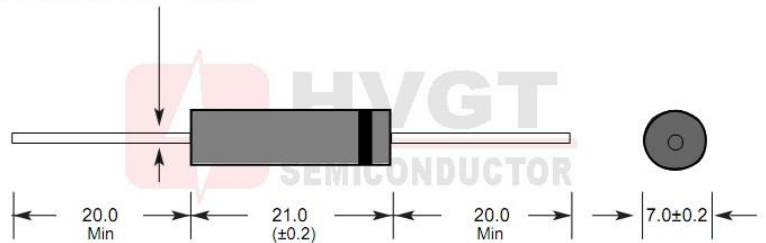
1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.1 grams (approx).

SHAPE DISPLAY:



SIZE: (Unit:mm) **HVGT NAME: DO-721**

DO-721 Series
Lead Diameter 1.2mm ±0.02



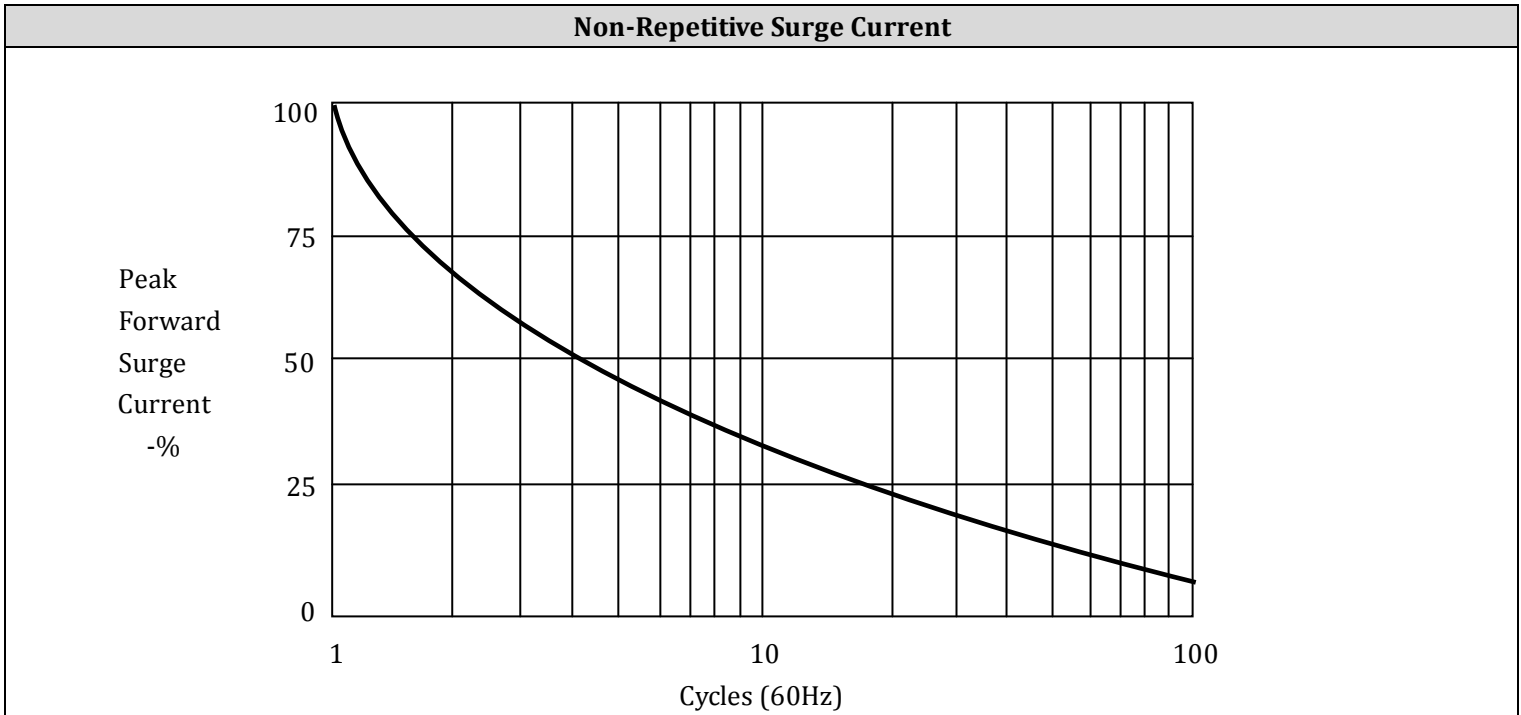
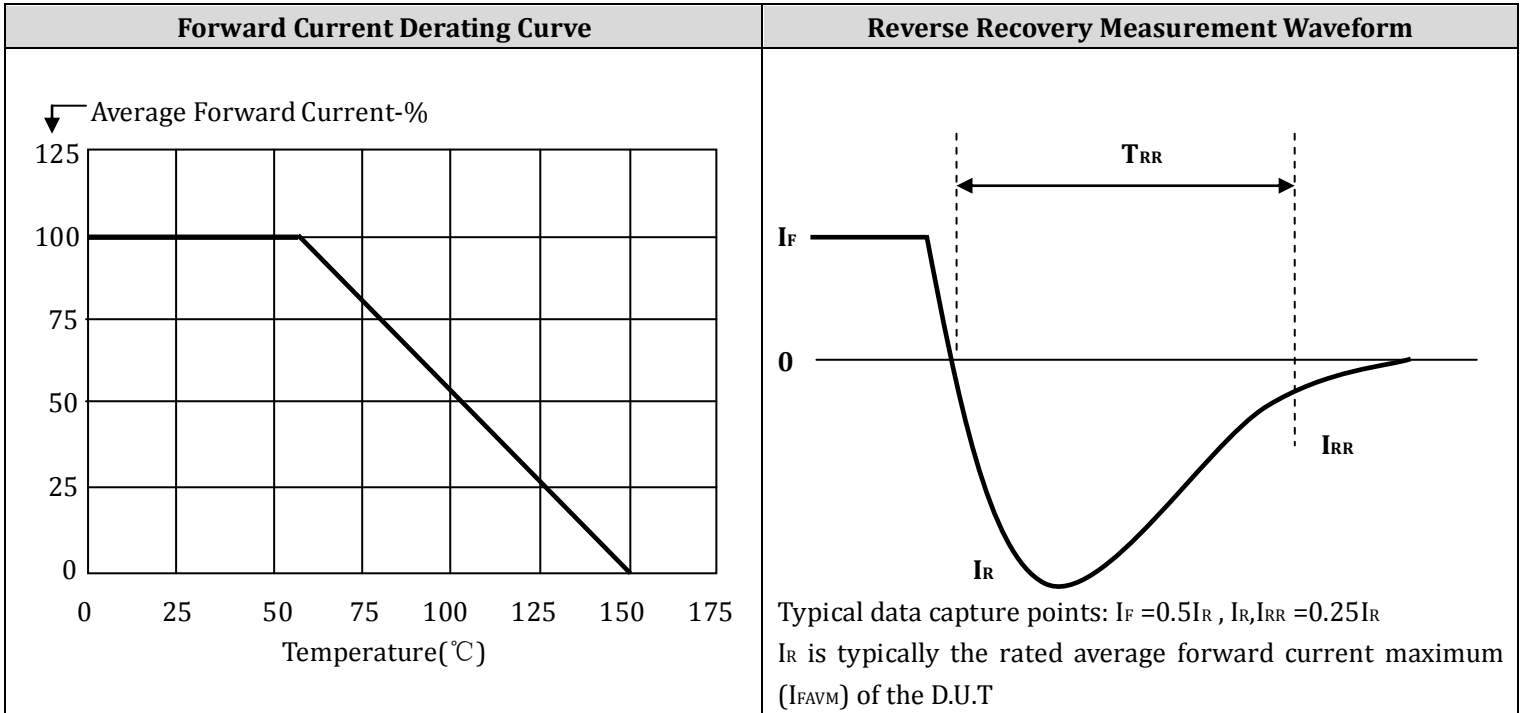
Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

| Items | Symbols | Condition | Data Value | Units |
|--------------------------------------|------------|--|------------|-------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | $T_A=25^{\circ}C$ | 12 | kV |
| Non-Repetitive Peak Reverse Voltage | V_{RSM} | $T_A=25^{\circ}C$ | -- | kV |
| Average Forward Current Maximum | I_{FAVM} | $T_A=55^{\circ}C$ | 450 | mA |
| | | $T_{OIL}=55^{\circ}C$ | -- | mA |
| Non-Repetitive Forward Surge Current | I_{FSM} | $T_A=25^{\circ}C$; 60Hz Half-Sine Wave; 8.3ms | 30 | A |
| Junction Temperature | T_J | | 150 | $^{\circ}C$ |
| Allowable Operation Case Temperature | T_C | | -40~+150 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | | -40~+150 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

| Items | Symbols | Condition | Data value | Units |
|-------------------------------|----------|---|------------|---------|
| Maximum Forward Voltage Drop | V_{FM} | at $25^{\circ}C$; at I_{FAVM} | 18 | V |
| Maximum Reverse Current | I_{R1} | at $25^{\circ}C$; at V_{RRM} | 2.0 | μA |
| | I_{R2} | at $100^{\circ}C$; at V_{RRM} | 50 | μA |
| Maximum Reverse Recovery Time | T_{RR} | at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$ | 100 | nS |
| Junction Capacitance | C_J | at $25^{\circ}C$; $V_R=0V$; $f=1MHz$ | 4.3 | pF |



| | Type | Code | Cathode Mark |
|----------------|----------|------------------|--------------|
| Marking | HV500F12 | HV500F12 HVGT | |